

isc N-Channel MOSFET Transistor
2SK3651-01R
FEATURES

- Drain Current : $I_D = 25A @ T_C = 25^\circ C$
- Drain Source Voltage
: $V_{DSS} = 200V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 100m\Omega (\text{Max}) @ V_{GS} = 10V$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

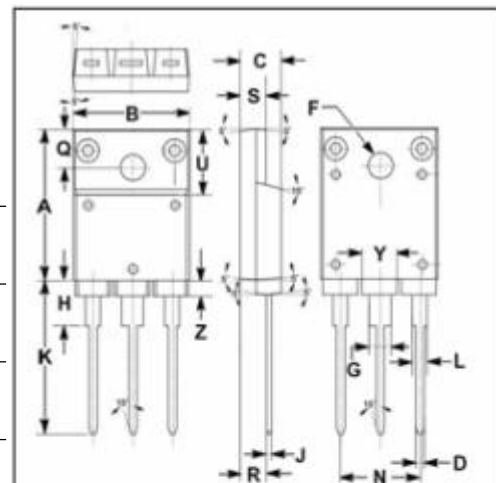
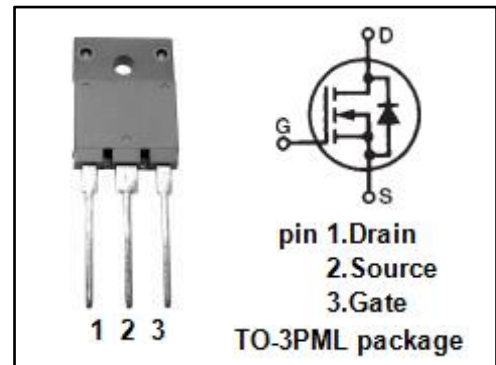
- motor drive, DC-DC converter, power switch and solenoid drive.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|----------------------------------------|----------|------------|
| V_{DSS} | Drain-Source Voltage | 200 | V |
| V_{GS} | Gate-Source Voltage-Continuous | ± 30 | V |
| I_D | Drain Current-Continuous | 25 | A |
| I_{DM} | Drain Current-Single Pluse | 100 | A |
| P_D | Total Dissipation @ $T_C = 25^\circ C$ | 85 | W |
| T_J | Max. Operating Junction Temperature | -55~150 | $^\circ C$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ C$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------|--------------------------------------|------|--------------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 1.47 | $^\circ C/W$ |



| DIM | mm | |
|-----|-------|-------|
| | MIN | MAX |
| A | 19.90 | 20.10 |
| B | 15.75 | 16.10 |
| C | 5.50 | 5.70 |
| D | 0.90 | 1.10 |
| F | 3.30 | 3.50 |
| G | 2.90 | 3.20 |
| H | 5.90 | 6.10 |
| J | 0.595 | 0.70 |
| K | 21.10 | 22.50 |
| L | 1.90 | 2.25 |
| N | 10.80 | 11.00 |
| O | 4.90 | 5.10 |
| R | 3.75 | 3.95 |
| S | 3.20 | 3.60 |
| U | 9.90 | 10.10 |
| Y | 4.20 | 4.90 |
| Z | 1.90 | 2.10 |

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|----------------------|---------------------------------|------------------------------------------------|-----|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.25mA | 250 | -- | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = 10V; I _D = 0.25mA | 3.0 | 5.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 12.5A | -- | 100 | mΩ |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±30V; V _{DS} = 0 | -- | ±0.1 | uA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 250V; V _{GS} = 0 | -- | 25 | uA |
| V _{SD} | Forward On-Voltage | I _S = 25A; V _{GS} = 0 | -- | 1.65 | V |

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